



# **Design and Analysis of a Gain-Tunable Low Noise Amplifier for Advanced Bio-Medical Systems**

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## Presentation outlines

- Introduction
- Application & Motivation
- Aims & Objectives
- Literature Review
- Methodology & System Details
- Results and Discussions
- Conclusion & Future works



# Introduction

A **Low Noise Amplifier (LNA)** is a specialized amplifier designed to boost weak signals while adding minimal noise.

## ❑ Working Principles:

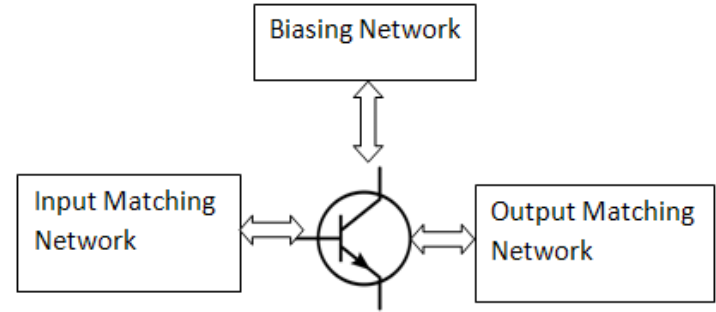
They **amplify** signals with minimal added noise, ensuring reliable signal processing.

## ❑ Key Performance Metrics:

LNAs are evaluated based on **noise figure, gain, power efficiency, and input impedance.**

## ❑ Design Focus:

**Efficient, compact, and low-power LNAs** are essential for advancing biomedical technology.



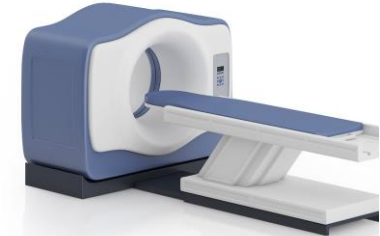
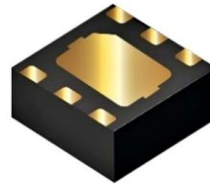
**Figure 01: Block Diagram of LNA**

**This research introduces a modified low noise amplifier architecture that integrates an attenuator, aimed at improving gain and intended for use in medical imaging applications.**



# Applications

- **Wireless communications**
  - Cell phone
  - Radio
  - Satellite
  - Wi-fi / Bluetooth
  - Military Communication
- **Medical Instruments**
- **Electronic Test Equipment**
- **Radar systems**
- **Earth Science Radiometry**



## Motivation

- To build a low noise amplifier which will minimize the noise while maximizing signal gain.
- Integrating an attenuator which will provide adjustable gain allowing the amplifier to adapt to different imaging applications.
- Using CMOS (Complementary Metal-Oxide-Semiconductor) technology in wideband low noise amplifiers offers several advantages



## Problem Statement

- From previous work we can see that different topology was used but their efficiency was not so good.
- Previous work was based on 3 stage amplifier, but their impedance matching is not so good, so their gain was not so high.
- There was problem on noise and also uses a large area of chip due to the number of reactive elements which can be obstacle to gain good performance on wideband low noise amplifier.
- There is no system for variable gain Amplifier in medical imaging technique.



## Research Objectives



To design a wide band low noise amplifier for **high frequency**.



To design **input and output matching network** for impedance matching.



To design an **attenuator** with the amplifier for **variable gain** in medical imaging.



To analyze the **performance** of the proposed amplifier for **high gain**.

| Theoretical overview                     |  |   |  |   |
|--|--|---|--|---|
| Parameters                               | Meaning  | Theoretical Working Range   | Implication if Below Range   | Implication if Above Range  |
| S11 (Input Return Loss)                  | Measure of how much power is <b>reflected back from the input</b> . Indicates input matching.              | $\leq -10$ dB (more negative is better)                             | Poor input matching; more power is reflected back, reducing efficiency       | Better input matching; less reflection, more power delivered to the LNA.                  |
| S12 (Reverse Isolation)                  | Measure of how much <b>signal leaks from output to input</b> .   | $\leq -20$ dB   | Poor reverse isolation; risk of instability or unwanted feedback.            | Better isolation; minimizes reverse signal leakage.                                       |
| S21 (Gain)                               | <b>Forward gain</b> of the amplifier; output/input signal strength.  | 10–30 dB  | Low amplification; weak signal output.                                       | High gain; may cause stability or linearity issues if excessive.                          |
| S22 (Output Return Loss)                 | Measures how well <b>the output is matched</b> .   | $\leq -10$ dB (more negative is better)                             | Poor output matching; more signal reflected from output, reducing efficiency | Better output matching; minimal reflection, more signal delivered to the load.            |
| Kf (Stability Factor)                    | Indicates amplifier stability; $K_f > 1$ implies <b>unconditional stability</b> .                          | $> 1$   | Risk of oscillation; unstable amplifier.                                     | Stable operation ensured.   |
| IIP3 (Input Third-Order Intercept Point) | A measure of <b>linearity</b> ; higher means better handling of strong signals <b>without distortion</b> . | $> 0$ dBm   | Poor linearity; more intermodulation distortion.                             | Better linearity; can handle stronger signals with minimal distortion.                    |
| Power Consumption                        | Total <b>DC power drawn</b> by the LNA   | As low as possible; typically $< 100$ mW for low-power applications | Lower is generally better, but too low may reduce performance.               | Higher power may offer better performance, but increases thermal issues and inefficiency. |



# Literature Review



## Review of Related Works

| Reference | Published Date | Publication Name  | Author name               |
|-----------|----------------|---|---------------------------|
| [3]       | May 1, 2015    | A low power and high gain CMOS LNA for UWB applications in 90 nm CMOS process | Sunil Pandey, Jawar Singh |

- Trade-offs between **trans-conductance** & **noise figure**.
- **Stability** conditions and **sensitivity**.

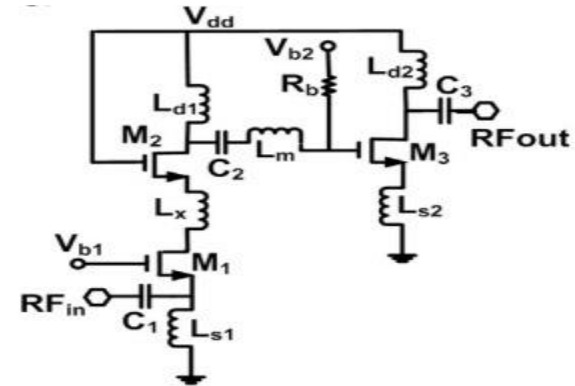


Figure 02: Common Source and Common Gate Cascaded LNA



## Review of Related Works

| Reference | Published Date   | Publication Name  | Author name   |
|-----------|------------------|---|---|
| [5]       | November 1, 2018 | Noise suppression in a common-gate UWB LNA with an inductor resonating at the source node | Hossein Sahoolizadeh,<br>Abumoslem Jannesari,<br>Massoud Dousti |

- Limitations of Increasing Voltage
- Complexity in designing input and output matching

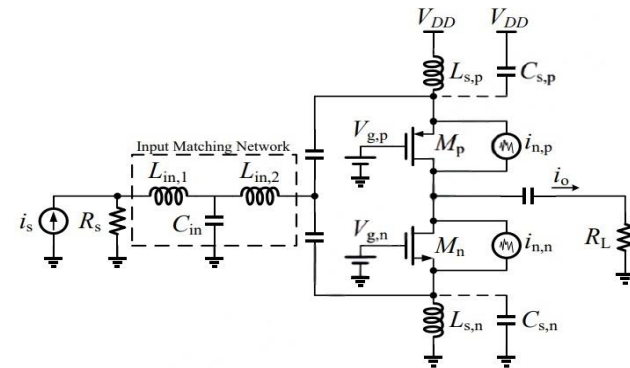


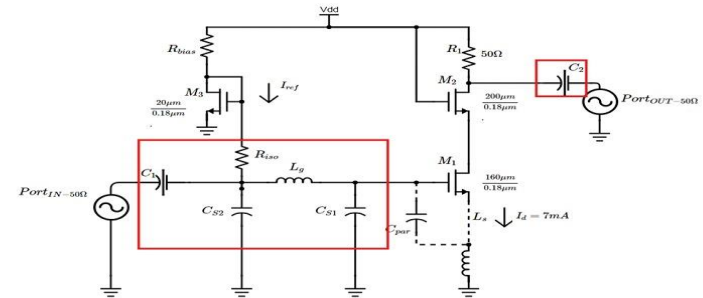
Figure 03: Common Gate LNA with biasing circuit



## Review of Related Works

| Reference | Published Date | Publication Name  | Author name    |
|-----------|----------------|---|----------------|
| [9]       | December 2024  | Design and optimization of a sub - 1dB noise figure low noise amplifier for magnetic resonance applications using CMOS technology | Bal, Ayşe Rana |

- Insufficient modeling of external components.
- High parasitic resistance and capacitance



**Fig 04: Cascade Common gate designed LNA with Biasing.**

## Review of Related Works

| Reference | CMOS Technology | Gain (dB) | Frequency Range (GHz) |
|-----------|-----------------|-----------|-----------------------|
| [1]       | 180 nm          | 16.1      | 0.1 – 1.4             |
| [2]       | 180 nm          | 13        | 2 – 5                 |
| [4]       | 90 nm           | 16        | 1.85 – 2.48           |
| [8]       | 130 nm          | 17        | 0.05 – 0.83           |



## Proposed Work

- Designing 90 nm technology using one common source amplifier and gate amplifier.

- Improving the gain performance of ultra wide band low noise amplifier by tuning technique.

- Achieving excellent impedance matching through the inclusion of the matching network. An improved impedance will help to increase gain and decreasing power return loss.

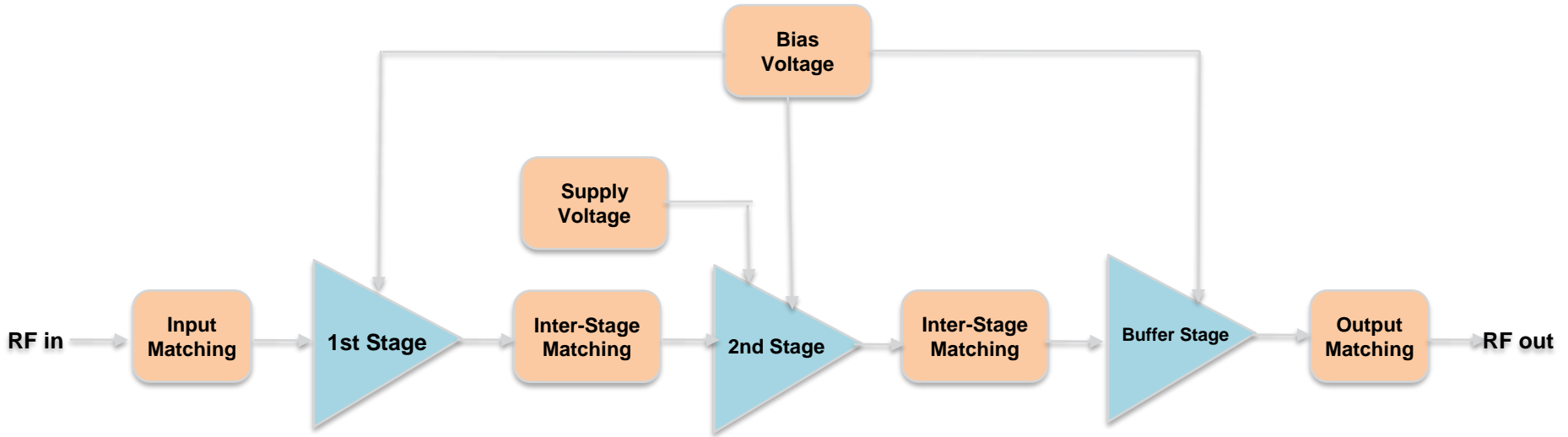
- Adding attenuator for variable gain in medical imaging.



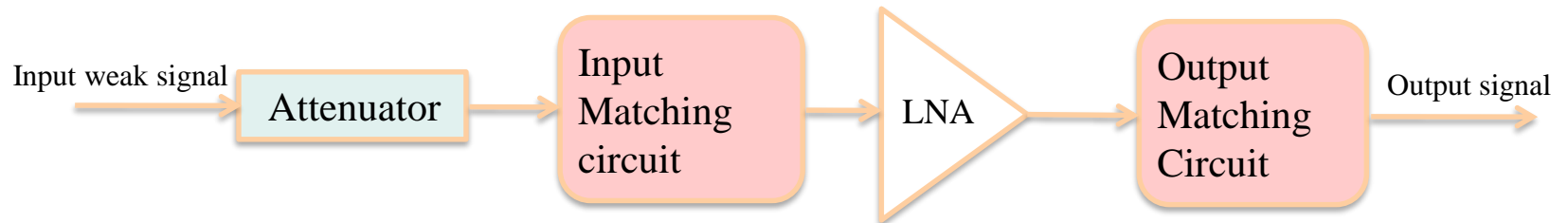


# Methodology

# Overview



**Figure 05(a): Block diagram of LNA design**



**Figure 05(b): Full circuit diagram**



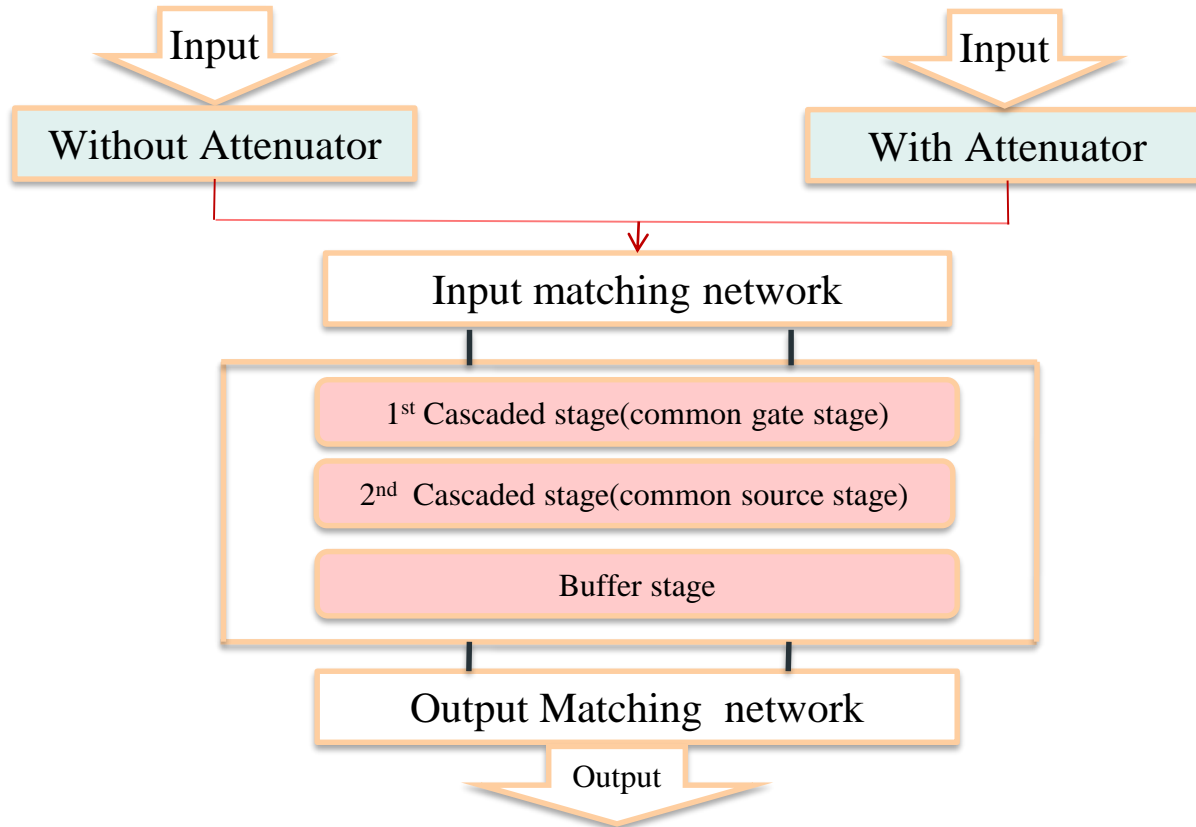


# System Design

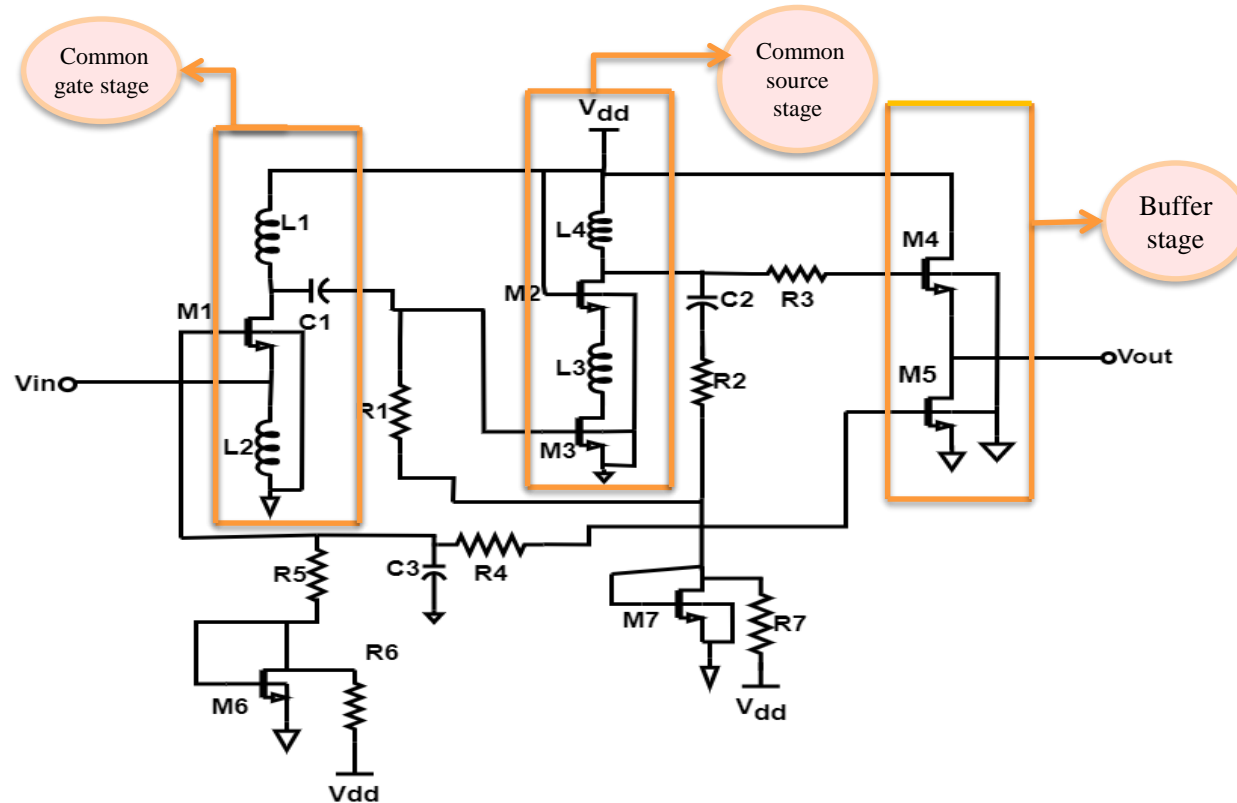
- To ensure **the most power transferred**, matching network are used to match the impedance from source to load.
- At first, we have to determine the **input and output impedance** value which can be done using simulation tools.
- The performance of the matching network is analyzed using simulation and this analyze include **bandwidth, return loss, gain**.



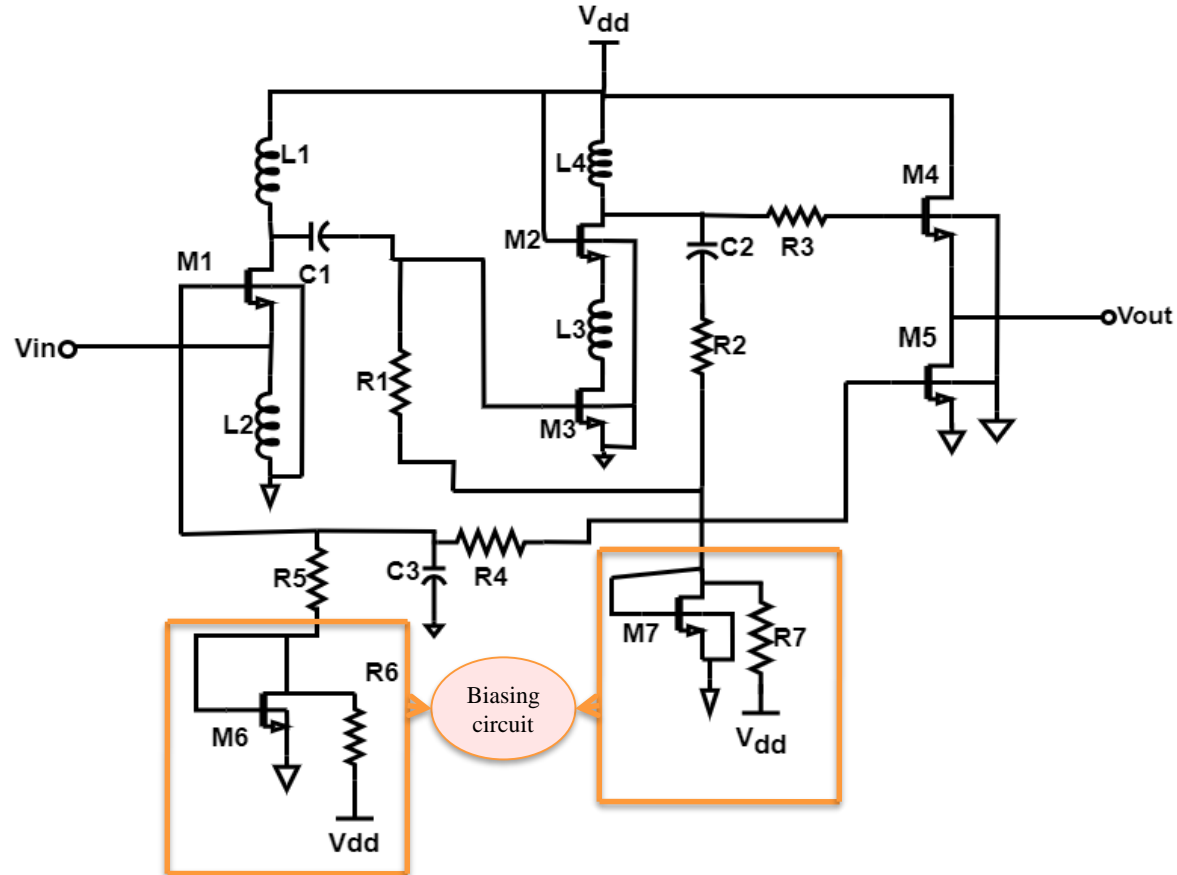
# Architecture of Proposed LNA



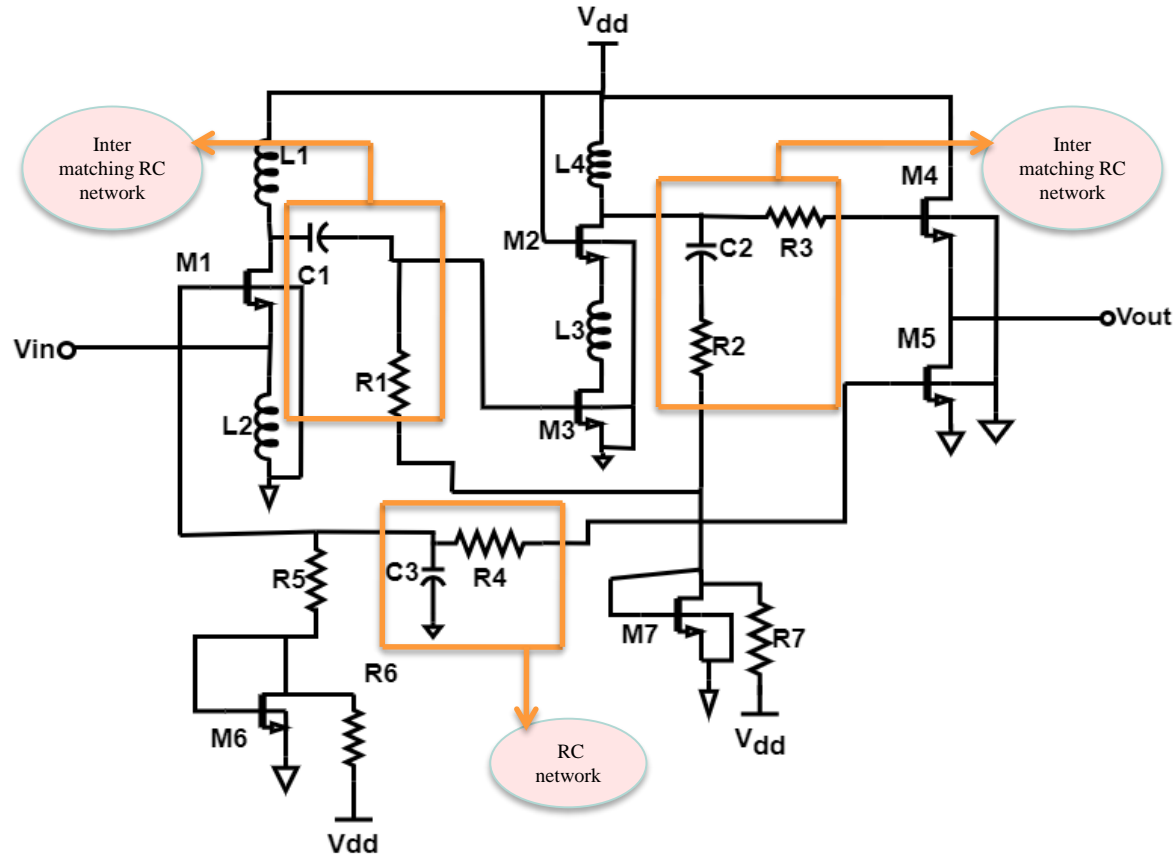
# Designed LNA Circuit Analysis



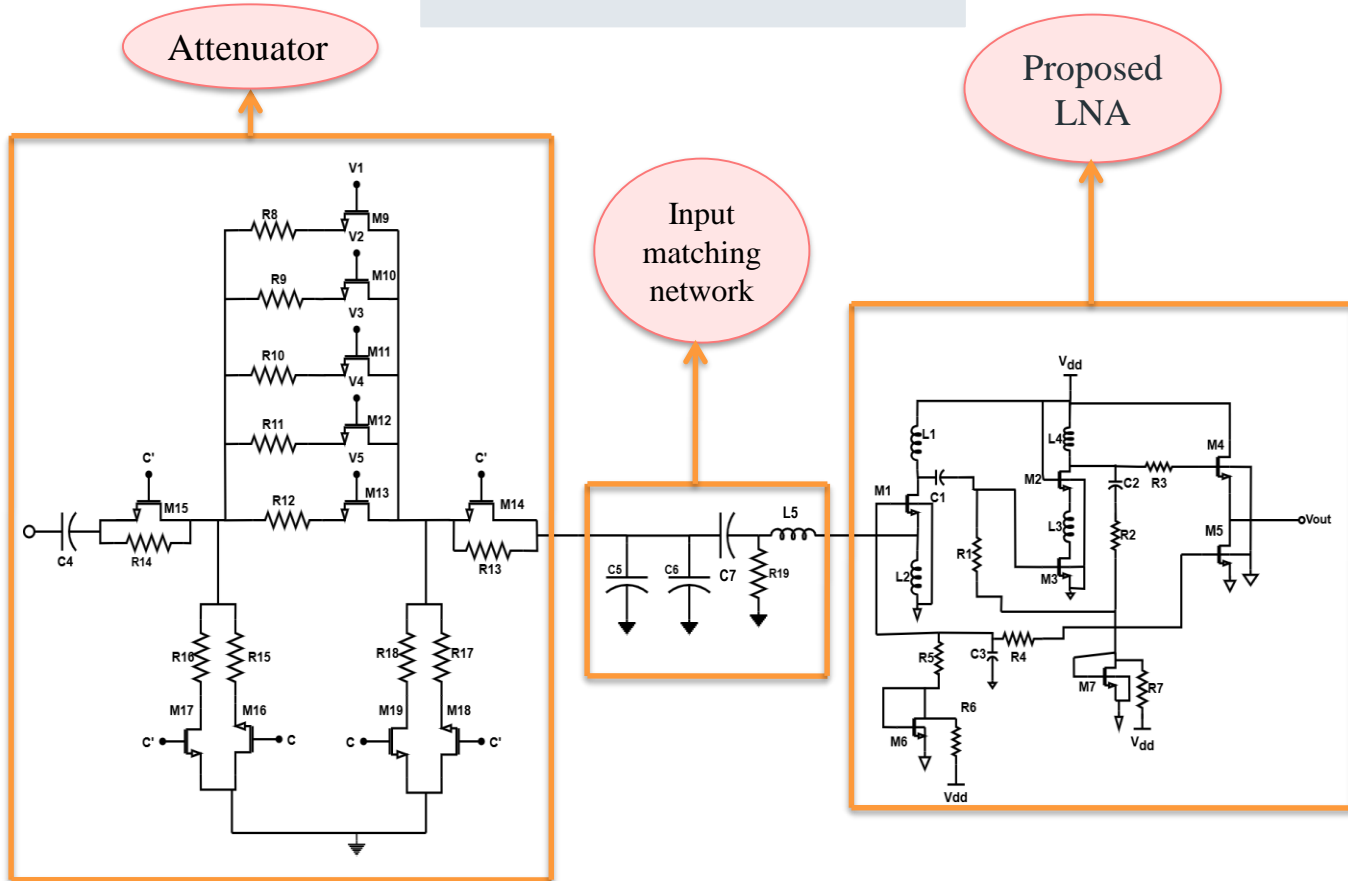
# Designed LNA Circuit Analysis



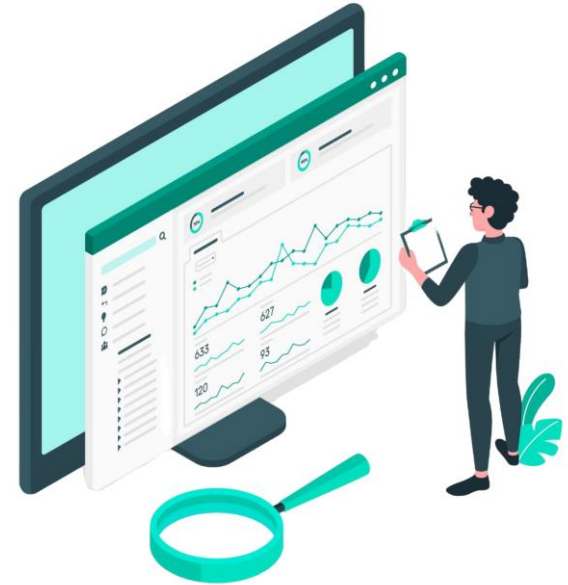
# Designed LNA Circuit Analysis



# Final Schematic



# Results & Discussion



## Key Findings

Our LNA **demonstrates excellent gain** of 29.21dB across the **operating frequency band**, ensuring reliable signal amplification.

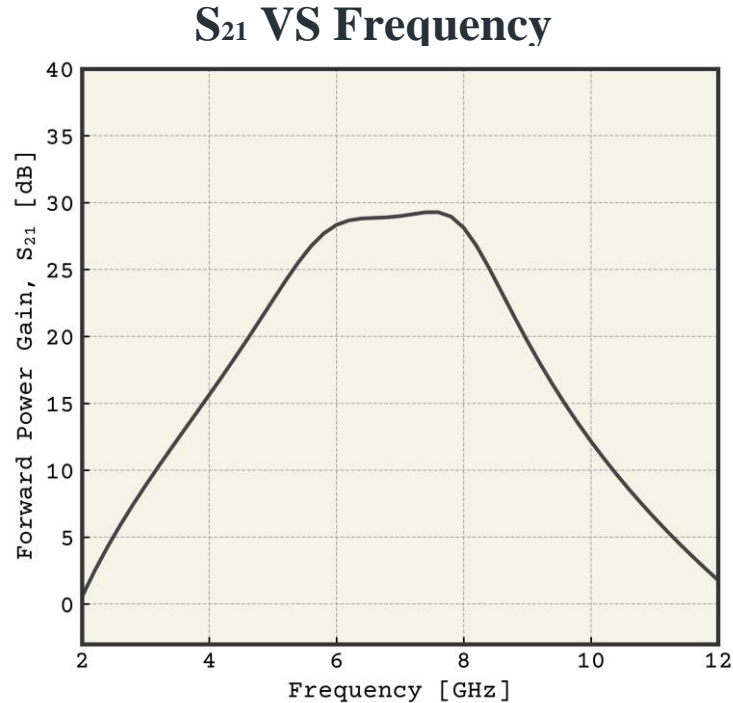
We demonstrated **Superior linearity (IIP3)** results in minimal distortion, preserving signal integrity and enabling high-fidelity amplification.

Additionally, we achieved **exceptional stability** maintaining consistent performance even under varying input power levels.





## Result Analysis : Power Gain



Observation

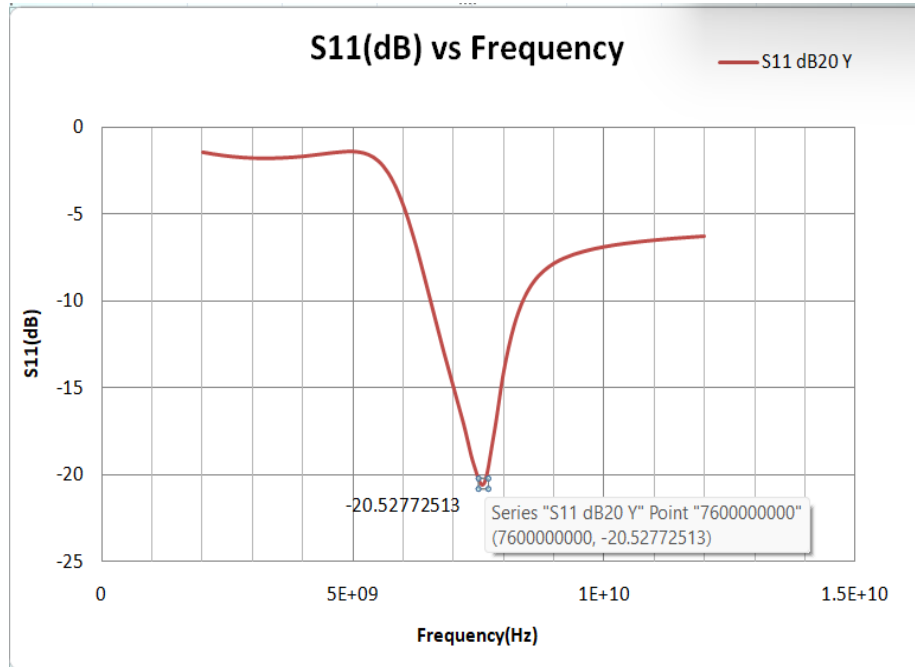
Maximum value of  **$S_{21}$**  parameter at **7.6 GHz** is **29.28 dB**

Showing a larger power gain (Output power is 631 times larger than the input power)

**Figure 06:  $S_{21}$  parameter of a two-stage Low noise amplifier**



## Result Analysis : Input Reflection Coefficient



Observation

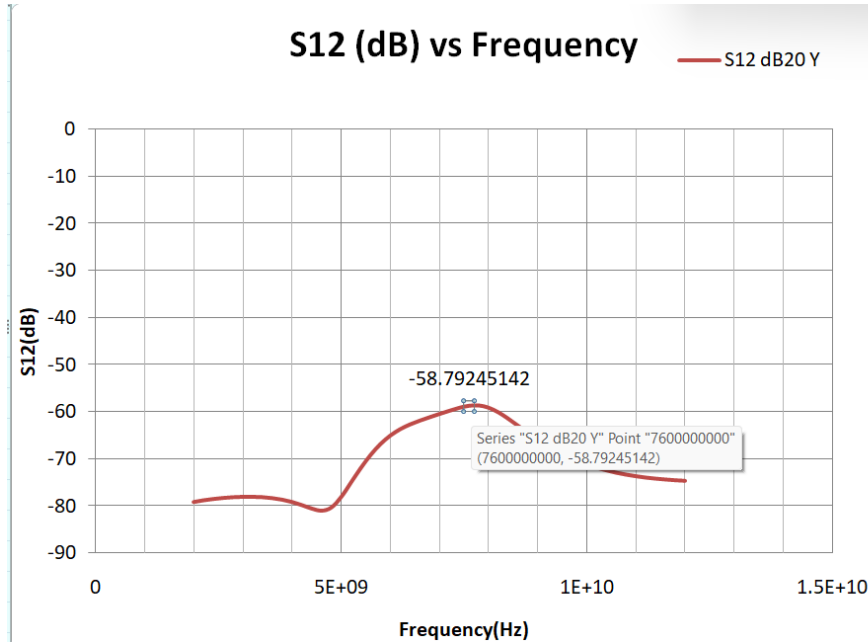
The value of **S11** parameter at **7.6 GHz** is **-20.528 dB**

Suggesting better input matching (Only small amount of power is reflected back at input port)

Figure 07: S11 parameter of a two-stage Low noise amplifier



## Result Analysis : Reverse Isolation



Observation

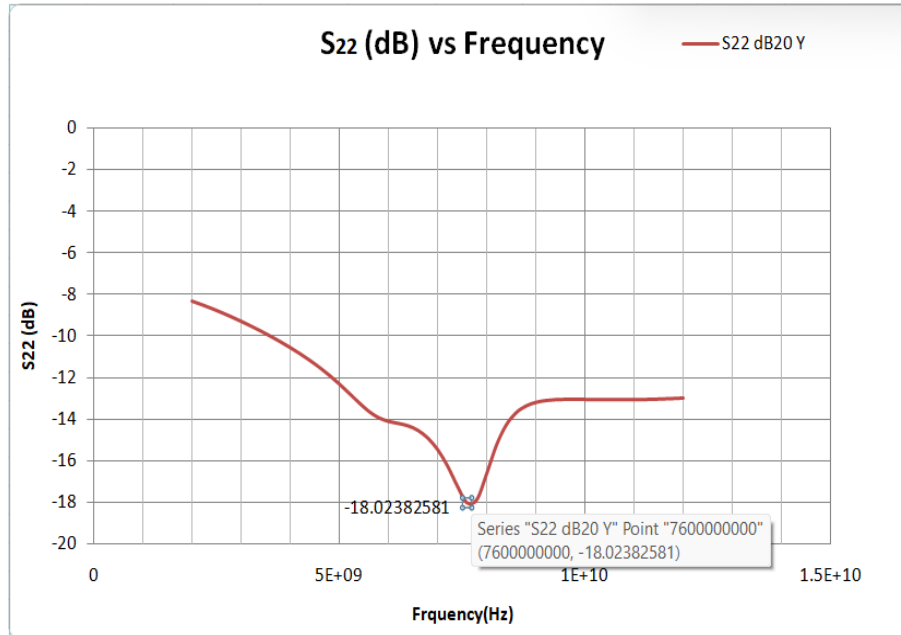
The value of **S12** parameter at **7.6 GHz** is **– 58.792 dB**

Showing good **reverse** isolation (little signal is leaking backward)

**Figure 08: S12 parameter of a two-stage Low noise amplifier**



## Result Analysis : Output Return Loss



Observation

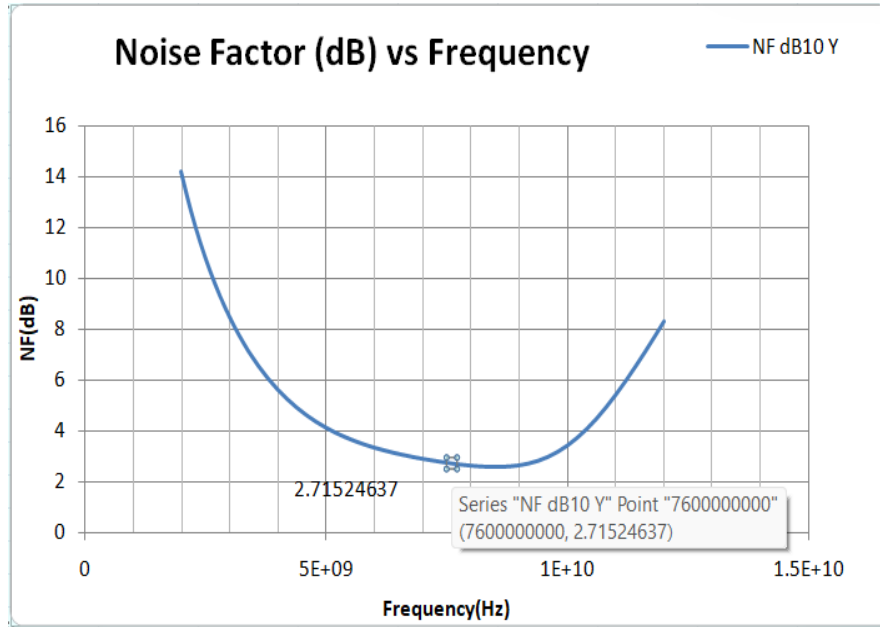
The value of **S22** parameter at **7.6 GHz** is **-18.024 dB**

Indicating good output matching (minor amount of output power is reflected back at output port)

Figure 09: S22 parameter of a two-stage Low noise amplifier



## Result Analysis : Noise Figure



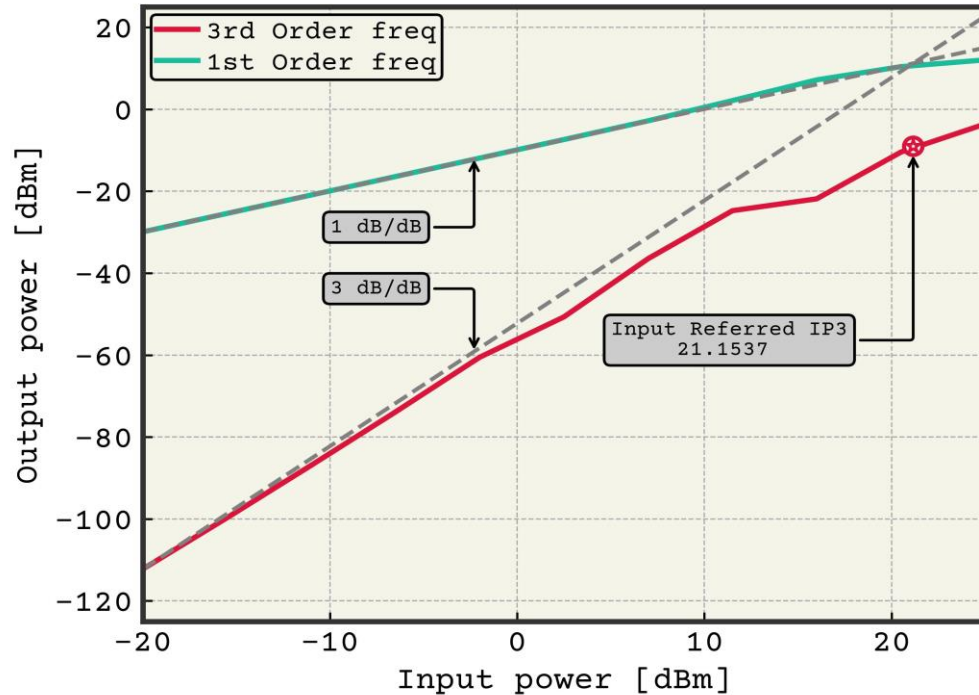
Observation

The value of Noise figure at **7.6 GHz** is **2.715 dB** (amplify signal without adding much additional noise)

Figure 10 : Noise parameter of a two-stage Low noise amplifier



## Result Analysis : IIP3 (Linearity)



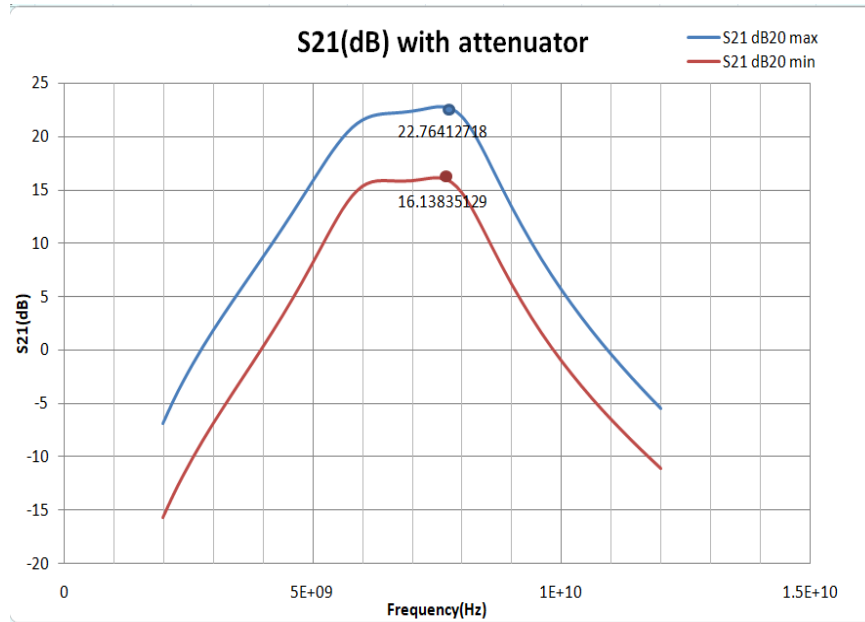
Observation

Here we found IIP3 is about **21.1537 dBm** which means that the proposed Low Noise Amplifier has **better linearity and less distortion.**

Figure 11: IIP3 (linearity result) of the proposed LNA



## Result Analysis : Variable Power Gain



Observation

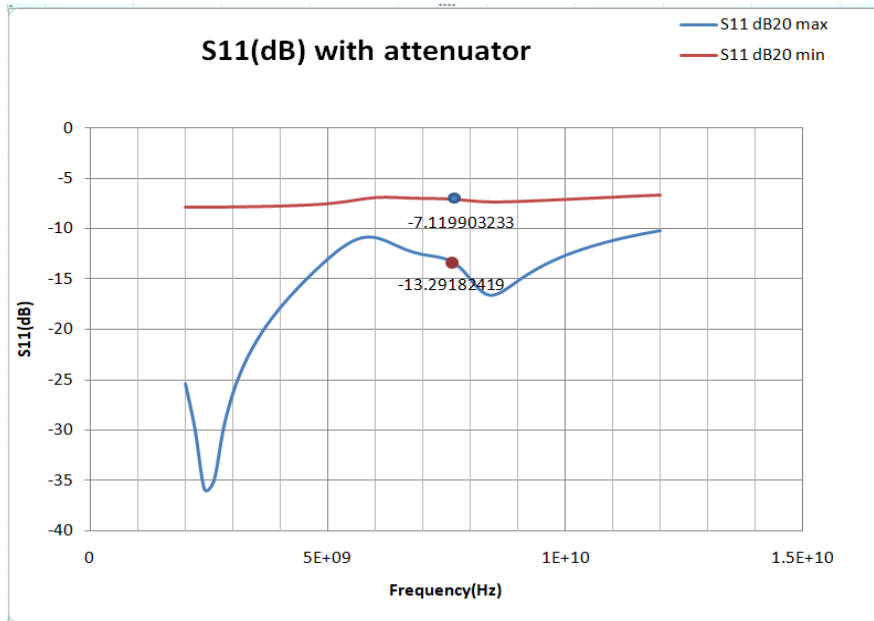
The value of S21 parameter at 7.6 GHz is verified from 15.97 dB to 22.7 dB

Showing good range of **variation** in power gain

**Figure 13: S21 parameter of a two-stage Low noise amplifier with attenuator**



## Result Analysis : Variable Input Reflection Coefficient



Observation

The value of S11 parameter at **7.6 GHz** is varied from **- 13.29 dB** to **-7.12 dB**

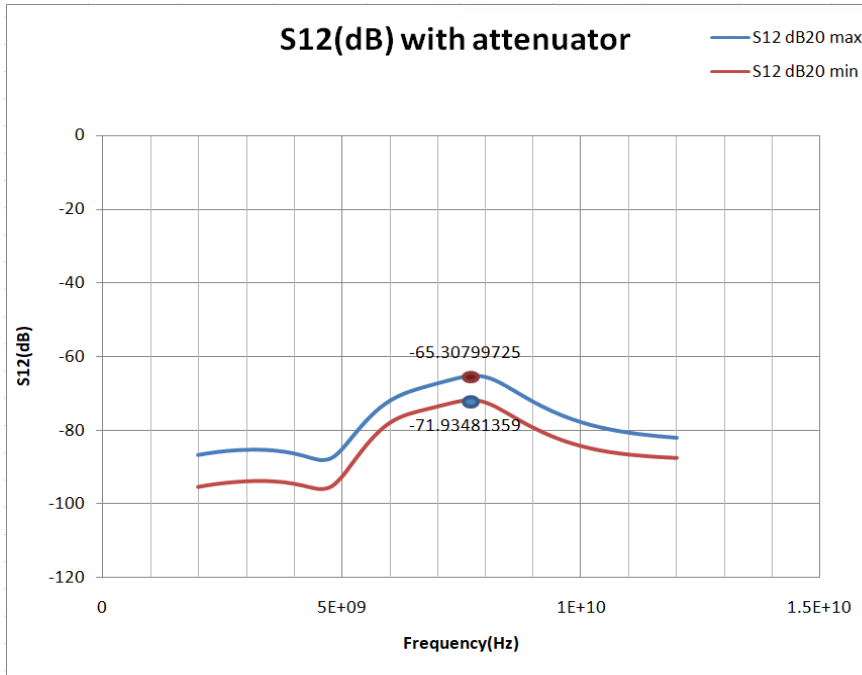
Suggesting **variable** better input matching

Figure 14: S11 parameter of a two-stage Low noise amplifier with attenuator





## Result Analysis : Variable Reverse Isolation



Observation

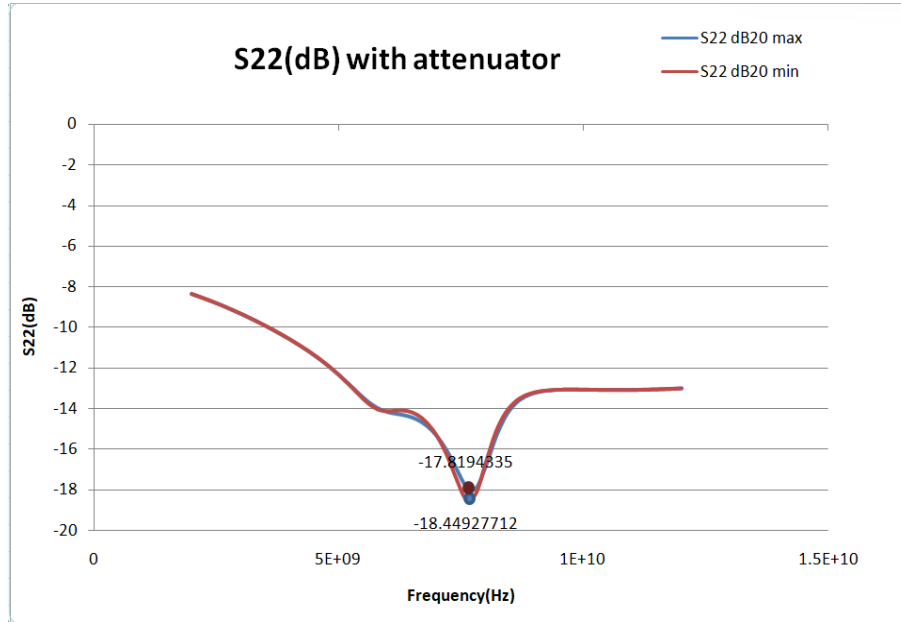
The value of **S12** parameter at **7.6 GHz** is **-71.935dB to -65.31dB**

Showing **variable** good reverse isolation

**Figure 16: S12 parameter of a two-stage Low noise amplifier with attenuator**



## Result Analysis : Variable Output Return Loss



Observation

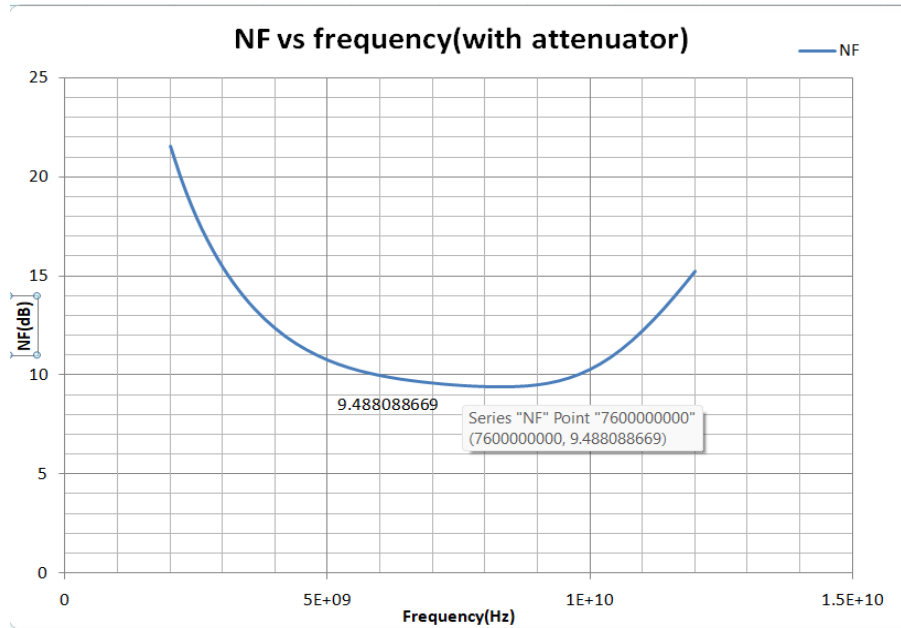
The value of S22 parameter at **7.6 GHz** is verified from **-18.45 dB** to **-17.82 dB**

Indicating **variable** good output matching

**Figure 15: S22 parameter of a two-stage Low noise amplifier with attenuator**



## Result Analysis : Noise Figure (with Attenuator)



Observation

The value of Noise figure at **7.6 GHz** is **9.488 dB**

**Figure 17: Noise parameter of a two-stage Low noise amplifier with attenuator**



# Conclusion



## Research Summery

### Performance parameter of the proposed LNA:

| Parameters          | This work (without attenuator) | This work (with attenuator) |
|---------------------|--------------------------------|-----------------------------|
| Technology          | 90nm                           | 90nm                        |
| Transistor Length   | 90nm                           | 90nm                        |
| Supply Voltage      | 1.2V                           | 1.2V                        |
| Operating Frequency | 7.6(GHz)                       | 7.6(GHz)                    |
| Gain(dB)            | 29.28                          | 22.7                        |
| Power Dissipation   | 83 mW                          | 83.45 mW                    |
| NF(dB)              | 2.715                          | 9.488                       |
| Kf                  | 10                             |                             |

**Considering the achieved performance, the proposed technique is suitable for the implementation of wideband LNAs in Biomedical application.**



## Contribution to the Work



### Designed LNA

The designed low-noise amplifier (LNA) enhances the circuit's linearity, gain, improving noise immunity and Bandwidth over a wide frequency range.



### Attenuator Integration

The attenuator adjusts the incoming signal level and enables variable gain to ensure the LNA operates within its optimal range.



### Design Performance

The proposed LNA circuit incorporates an attenuator and a common-gate common-source (CG-CS) stage, which together optimize power consumption, gain control, noise performance, and bandwidth. Body biasing improves S-parameters, enhances gain and reduces output noise.

## Comparison with Previous Work

| Reference                      | CMOS Tech. (nm) | Supply Voltage | Gain (dB)  | Frequency (GHz) | S11 (dB)        | S12 (dB)         | S22(dB)          | IIP3 (dBm) |
|--------------------------------|-----------------|----------------|------------|-----------------|-----------------|------------------|------------------|------------|
| This Work (without attenuator) | 90nm            | 1.2V           | 29.25      | 7.616           | -20.31          | -58.78           | -18.01           | 21.1537    |
| This Work (with attenuator)    | 90nm            | 1.2V           | 15.97-22.7 | 7.616           | -13.52 to -7.08 | -71.93 to -65.24 | -18.34 to -17.86 |            |
| [2]                            | 180             | 1.8V           | 13         | 2 - 5           | < -10           | ---              | ----             | -9.5       |
| [8]                            | 130             | 1.8V           | 17         | 0.05-0.83       | < -8.9          | ----             | <-8.5            | -6.3       |
| [1]                            | 180             | 1.8            | 16.1       | 0.1 - 1.4       | < -9            | -----            | -----            | 13-18.9    |



## Future Work



Designing the **Layout** of the proposed Low Noise Amplifier

**Implementation and fabrication** of the designed LNA

Real-World **Validation** and **Expansion**



## References

- [1] "A 0.1–1.4 GHz inductorless low-noise amplifier with 13 dBm IIP3 and 24 dBm IIP2 in 180 nm CMOS," Benqing Guo, Jun Chen, Hongpeng Chen and Xuebing Wang, *Modern Physics Letters B*, pp.1850009, vol. 32, no 2, January 20, 2018.
- [2] "A wideband 2–5 GHz noise canceling subthreshold low noise amplifier," A.R. Aravinth Kumar, Bibhu Datta Sahoo and Ashudeb Dutta, *IEEE Transactions on Circuits and Systems II: Express Briefs*, pp. 834-838, vol. 65, no. 7, June 26, 2017.
- [3] "A low power and high gain CMOS LNA for UWB applications in a 90 nm CMOS process." Sunil Pandey, Jawar Singh. *Microelectronics Journal*, vol. 46, no. 5, pp. 390-397, May 1, 2015.
- [4] "Design of a 1-V 90-nm CMOS adaptive LNA for multi-standard wireless receivers" Becerra-Alvarez, E. C., Sandoval-Ibarra, F., & de La Rosa, J. M, *Revista mexicana de física*, pp. 322-328, vol. 54, issue. 4, 2015.
- [5] "Noise suppression in a common-gate UWB LNA with an inductor resonating at the source node," Hossein Sahoolizadeh, Abumoslem Jannesari, Massoud Dousti, *AEU International Journal of Electronics and Communications*, vol. 96, pp. 144-153, November 1, 2018.
- [6] "A Wideband Noise-Canceling CMOS LNA With Enhanced Linearity by Using Complementary nMOS and pMOS Configurations," Benqing Guo, Jun Chen, Lei li, Haiyan Jin, Guoning Yang, *IEEE Journal of Solid-State Circuits*, pp. 1331-1344, vol. 52, no. 5, May 4, 2018.
- [7] "A Low Power Low Noise Amplifier for Biomedical Applications," Deepansh Dubey, Anu Gupta, *2015 IEEE International Conference on Electrical, Computer and Communication Technologies (ICECCT)*, pp. 1-6, vol. 52, no. 5, March 5, 2015.
- [8] "50–830 MHz noise and distortion canceling CMOS low noise amplifier," Sana Arshada, Rashad Ramzanb, Qamar-ul Wahabc, *Integration*, pp.63-73 vol. 60, January 1, 2018.
- [9] Bal, Ayşe Rana, "Design and optimization of a sub - 1dB noise figure low noise amplifier for magnetic resonance applications using CMOS technology," PhD diss., December 2024.



## Image Sources

- ◉ <https://maurymw.com/applications/noise-figure-noise-parameters-extraction/>
- ◉ <https://www.linkedin.com/pulse/development-wireless-communication-sriram-s-aqzsc/>
- ◉ <https://pixabay.com/vectors/antenna-parabolic-reflector-307223/>
- ◉ <https://cgaxis.com/product/mri-scanner/>
- ◉ <https://www.microwavejournal.com/articles/40855-teledyne-e2v-hirel-releases-ultra-low-noise-amplifier-for-space-applications>
- ◉ <https://www.aliexpress.us/item/3256802720168498.html?gatewayAdapt=glo2usa4itemAdapt>



# Thank You

*Please let us know if you have any questions !*

